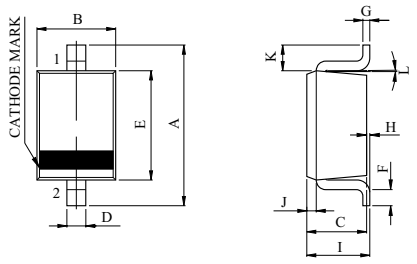
KDZ9.3V

ZENER DIODE
SILICON EPITAXIAL PLANAR DIODE

CONSTANT VOLTAGE REGULATION APPLICATION.

FEATURES

- Small Package
- Normal Voltage Tolerance about ±2%.



DIM	MILLIMETERS
A	2.50±0.1
B	1.25±0.05
C	0.90±0.05
D	0.30+0.06/-0.04
E	1.70±0.05
F	MIN 0.17
G	0.126±0.03
H	0~0.1
I	1.0 MAX
J	0.15±0.05
K	0.4±0.05
L	2°+4/-2
M	4~6°

1. ANODE
2. CATHODE

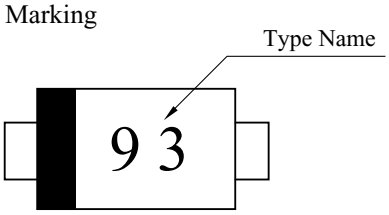
USC

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	P_D *	200*	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

* Mounted on a glass epoxy circuit board of 20×20㎜,
pad dimension of 4×4㎜.

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zener Voltage	V_Z	I_Z=5mA	9.1	-	9.5	V
Dynamic Impedance	Z_Z	I_Z=5mA	-	-	18	Ω
Knee Dynamic Impedance	Z_{ZK}	I_Z=0.5mA	-	-	120	Ω
Reverse Current	I_R	V_R=7V	-	-	0.5	μA